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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/826,507	04/16/2004	Volker A. Blaschke	0150139	1937

7590 08/24/2005

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EXAMINER

CHIU, TSZ K

ART UNIT	PAPER NUMBER
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2822

DATE MAILED: 08/24/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/826,507

Applicant(s)

BLASCHKE ET AL.

Examiner

Tsz K. Chiu

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on April 16, 2004.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-21 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☐ Claim(s) 1-21 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date April 16, 2004.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-21 rejected under 35 U.S.C. 102(b) as being anticipated by Maeda et. al. (6,452,29H).

With respect to claim 1, Maeda discloses an active shield (101, Fig. 1) situated in a substrate (1, Fig. 1), said active shield comprising a salicide layer (column 15, lines 14-15) situated on an active region, said active shield having a first conductivity type (column 3, lines 41-42); a passive component (SI, Fig. 8) situated in an interconnect metal layer in (CP, Fig. 8) said semiconductor die, said passive component being situated above said active shield (SI, Fig.8); wherein said active shield defines an AC ground (101, Fig. 2) for said passive component.

With respect to claim 2, Maeda discloses at least one contact connecting said active shield (101, Fig. 2) to a semiconductor die AC ground.

With respect to claim 3, Maeda discloses a well situated in said substrate (NW, Fig. 40), said active shield being situated in said well (274, Fig. 20), said well having a second conductivity type (NW, Fig. 40).

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With respect to claim 4, Maeda discloses active shield comprises a plurality of fingers (21L and 21S, Fig. 2), each of said plurality of fingers comprising a salicide segment situated on an active segment (column 15, lines 14-15).

With respect to claim 5, Maeda discloses passive component is an inductor (SI, Fig. 70).

With respect to claim 6, Maeda discloses a salicided active region situated in said well, said salicided active region being situated adjacent to at least one side of said active shield (Fig. 40), said salicided active region having said second conductivity type (272, Fig. 20).

With respect to claim 7, Maeda discloses salicide layer is selected from the group consisting of titanium silicide, cobalt silicide, and nickel mono-silicide (column 17, lines 46-47).

With respect to claim 8, Maeda discloses well is connected to a voltage source (V_{cc} , Fig. 40), said voltage source being greater than or equal to ground voltage, said voltage source having no AC component (Fig. 16).

With respect to claim 9, Maeda discloses a well situated in said substrate (NW, Fig. 40), said active shield being situated in said well (272, Fig. 20), said well having said first conductivity type (NW, Fig. 40).

With respect to claim 10, Maeda discloses a well situated in a substrate (Fig. 40), said well having a first conductivity type (NW, Fig. 40); an active shield situated in said well (272, Fig. 20), said active shield comprising a salicide layer (column 15, lines 14-15) situated on an active region in said well (121 and NW,

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Fig. 40), said active shield having a second conductivity type (121, Fig. 40); a passive component (SI, Fig. 70) situated in an interconnect metal layer (CP, Fig. 70) in said semiconductor die, said passive component (SI, Fig. 1) being situated above said active shield (101, Fig. 1); wherein said active shield defines an AC ground (101, Fig. 2) for said passive component.

With respect to claim 11, Maeda discloses at least one contact connecting said active shield (101, Fig. 2) to a semiconductor die AC ground.

With respect to claim 12, Maeda discloses active shield comprises a plurality of fingers (21L and 21S, Fig. 2), each of said plurality of fingers comprising a salicide segment situated on an active segment (column 15, lines 14-15).

With respect to claim 13, Maeda discloses a salicided active region situated adjacent to at least one side of said active shield (Fig. 40), said salicided active region having a first conductivity type (272, Fig. 20).

With respect to claim 14, Maeda discloses passive component is an inductor (SI, Fig. 70).

With respect to claim 15, Maeda discloses salicided active region is connected to a voltage source (V_{cc} , Fig. 16), said voltage source being greater than or equal to ground voltage, said voltage source having no AC component (Fig. 16).

With respect to claim 16, Maeda discloses salicide layer is selected from the group consisting of titanium silicide, cobalt silicide, and nickel mono-silicide (column 17, lines 46-47).

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With respect to claim 17, Maeda discloses a well situated in a substrate (NW, Fig. 40), said well having a first conductivity type (column 45, line 19); an active shield situated in said well (274, Fig. 20), said active shield comprising a plurality of fingers (21L and 21S, Fig. 2), each of said plurality of fingers comprising a salicide segment situated on an active segment (column 15, lines 14-15), said plurality of fingers having a second conductivity type (278, Fig. 20); a passive component situated in an interconnect metal layer in said semiconductor die (SI, Fig. 70), said passive component being situated above said active shield (101, Fig. 1); wherein said active shield defines an AC ground (101, Fig. 2) for said passive component.

With respect to claim 18, Maeda discloses at least one contact connecting said active shield (101, Fig. 2) to a semiconductor die AC ground.

With respect to claim 19, Maeda discloses a salicided active region situated adjacent to at least one side of said active shield (Fig. 40), said salicided active region having said first conductivity type (272, Fig. 40).

With respect to claim 20, Maeda discloses the passive component is an inductor (SI, Fig. 70), wherein said plurality of fingers terminate an electric field of said inductor (column 16, lines 30-39).

With respect to claim 21, Maeda discloses salicided active region is connected to a voltage source (V_{cc} , Fig. 16), said voltage source being greater than or equal to ground voltage, said voltage source having no AC component (Fig. 16).


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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tsz K. Chiu whose telephone number is 517-272-8656. The examiner can normally be reached on 0800 to 1700.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TKC



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